

IN THE CLAIMS

1. (Currently Amended) A surface acoustic wave device comprising:
 - a piezoelectric substrate on which at least two resonators having comb-like electrodes are formed; and
 - a silicon substrate that is directly bonded to the piezoelectric substrate and is less expansive than the piezoelectric substrate, wherein under each of said at least two resonators
~~a cavity is being formed in the silicon substrate and being located below at least one of the resonators.~~
2. (Currently Amended) The surface acoustic wave device as claimed in claim 1, wherein said one each of the at least two resonators has reflector electrodes close to the comb-like electrodes thereof, and the cavity is located below the comb-like electrodes and the reflector electrodes.
3. (Currently Amended) The surface acoustic wave device as claimed in claim 1, wherein the cavity is formed in the silicon substrate and is located below only an area that includes the comb-like electrodes of a corresponding one of the at least two resonators.
4. (Original) The surface acoustic wave device as claimed in claim 1, wherein the piezoelectric surface has a rough surface that is exposed through the cavity.

5. (Original) The surface acoustic wave device as claimed in claim 1, further comprising an acoustic absorption member provided on a surface portion of the piezoelectric substrate exposed through the cavity.

6. (Currently Amended) The surface acoustic wave device as claimed in claim 1, further comprising another resonator wherein no cavity is cavities are formed in the silicon substrate and are located below said another resonator only some comb-like electrodes.

7. (Original) The surface acoustic wave device according to claim 1, wherein the piezoelectric substrate is made of one of lithium tantalate and lithium niobate.

8. (Withdrawn and Currently Amended) The A surface acoustic wave device comprising: as claimed in claim 1, wherein
a piezoelectric substrate on which resonators having comb-like electrodes are formed; and
a the silicon substrate that is directly bonded to the piezoelectric substrate and is less expansive than the piezoelectric substrate; and
the silicon substrate has having a resistivity equal to or greater than $10 \Omega \cdot \text{cm}$.

9. (Withdrawn and Currently Amended) The A surface acoustic wave device comprising: as claimed in claim 1, wherein

~~a piezoelectric substrate on which resonators having comb-like electrodes are formed; and~~

the a-silicon substrate that is directly bonded to the piezoelectric substrate and is less expansive than the piezoelectric substrate,

the resonators are being located at a distance d from ends of the device in a direction in which a surface acoustic wave propagates, and

the distance d satisfies satisfying $d \geq 3tp$ where tp is a thickness of the piezoelectric substrate.

10. (Original) The surface acoustic wave device as claimed in claim 1, further comprising electrode pads provided on the piezoelectric substrate and electrically coupled to the resonators.

11. (Withdrawn) A method of fabricating a surface acoustic wave device comprising the steps of: directly bonding a piezoelectric substrate on which resonators having comb-like electrodes are formed, and a silicon substrate that is directly bonded to the piezoelectric substrate and is less expansive than the piezoelectric substrate; and forming a cavity in the silicon substrate so that the cavity is located below at least one of the resonators.

12. (Withdrawn) The method as claimed in claim 11, wherein said one of the resonators has reflector electrodes close to the comb-like electrodes thereof, and the step of forming a cavity forms the cavity that is located below the comb-like electrodes

and the reflector electrodes.

13. (Withdrawn) The method as claimed in claim 11, further comprising a step of making a surface portion of the piezoelectric substrate exposed through the cavity rough.

14. (Withdrawn) The method as claimed in claim 11, further comprising a step of providing an acoustic absorption member on a surface portion of the piezoelectric substrate exposed through the cavity.

15. (Withdrawn) The method as claimed in claim 11, wherein the step of forming a cavity comprises a step of forming a plurality of cavities located below only some resonators.

16. (Withdrawn) The method as claimed in claim 11, wherein the step of forming a cavity comprises a step of etching the silicon substrate from a first side thereof opposite to a second side thereof on which the piezoelectric substrate is provided.

17. (Withdrawn) The method as claimed in claim 11, wherein the step of forming a cavity etches the silicon substrate by RIE.

18. (Withdrawn) The method as claimed in claim 11, wherein the piezoelectric substrate is made of one of lithium tantalate and lithium niobate.

19. (Withdrawn) A method of fabricating a surface acoustic wave device comprising the steps of: directly bonding a piezoelectric substrate and a substrate that is less expansive than the piezoelectric substrate; and forming resonators on the piezoelectric substrate so as to be located at a distance d from ends of the device in a direction in which a surface acoustic wave propagates, the distance d satisfying $d \geq 3 t_p$ where t_p is a thickness of the piezoelectric substrate.